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FDS6679

30 Volt P-Channel PowerTrench® MOSFET

General Description

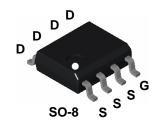
This P-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers, and battery chargers.

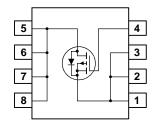
These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable $R_{\text{DS(ON)}}$ specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

Features

- -13 A, -30 V. $R_{DS(ON)} = 9 \text{ m}\Omega$ @ $V_{GS} = -10 \text{ V}$ $R_{DS(ON)} = 13 \text{ m}\Omega$ @ $V_{GS} = -4.5 \text{ V}$
- Extended V_{GSS} range ($\pm 25 \text{V}$) for battery applications
- High performance trench technology for extremely low $R_{\mbox{\scriptsize DS(ON)}}$
- · High power and current handling capability





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		-30	V
V _{GSS}	Gate-Source Voltage		±25	V
I _D	Drain Current - Continuous	(Note 1a)	-13	А
	- Pulsed		-50	
P _D	Power Dissipation for Single Operation	(Note 1a)	2.5	W
		(Note 1b)	1.2	
		(Note 1c)	1.0	
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +175	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	50	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case	(Note 1)	25	°C/W

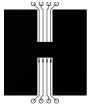
Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS6679	FDS6679	13"	12mm	2500 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics	1	I	I	I	I
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-30			V
ΔBV _{DSS} ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = -250 μA, Referenced to 25°C		-23		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μА
I _{GSS}	Gate-Body Leakage	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA
On Char	acteristics (Note 2)		•	•		•
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-1	-1.6	-3	V
$\Delta V_{GS(th)} \over \Delta T_J$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \mu A$, Referenced to 25°C		5		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$V_{GS} = -10 \text{ V}, \qquad I_D = -13 \text{ A}$ $V_{GS} = -4.5 \text{ V}, \qquad I_D = -11 \text{ A}$ $V_{GS} = -10 \text{ V}, I_D = -13 \text{ A}, T_J = 125 ^{\circ}\text{C}$		7.3 10 9.5	9 13 13	mΩ
I _{D(on)}	On-State Drain Current	$V_{GS} = -10 \text{ V}, \qquad V_{DS} = -5 \text{ V}$	-50			Α
g _{FS}	Forward Transconductance	$V_{DS} = -5 \text{ V}, \qquad I_{D} = -13 \text{ A}$		44		S
Dynamic	Characteristics			•		
C _{iss}	Input Capacitance	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V},$		3939		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		972		pF
C _{rss}	Reverse Transfer Capacitance			498		pF
Switchir	ng Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = -15 \text{ V}, \qquad I_{D} = -1 \text{ A}, \\ V_{GS} = -10 \text{ V}, \qquad R_{GEN} = 6 \Omega$		19	34	ns
t _r	Turn-On Rise Time			10	20	ns
t _{d(off)}	Turn-Off Delay Time	1		110	176	ns
t _f	Turn-Off Fall Time	7		65	104	ns
Q _g	Total Gate Charge	$V_{DS} = -15 \text{ V}, \qquad I_{D} = -13 \text{ A},$		71	100	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = -10 \text{ V}$		12		nC
Q_{gd}	Gate-Drain Charge	<u> </u>		15		nC
Drain-S	ource Diode Characteristics	and Maximum Ratings				
Is	Maximum Continuous Drain-Source				-2.1	Α
V _{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = -2.1 \text{ A} \text{(Note 2)}$		-0.7	-1.2	V

Notes

 R_{0,JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{0,JC} is guaranteed by design while R_{0,CA} is determined by the user's board design.



a) 50°C/W (10 sec) 62.5°C/W steady state when mounted on a 1in² pad of 2 oz copper



b) 105°C/W when mounted on a .04 in² pad of 2 oz copper



c) 125°C/W when mounted on a minimum pad.

Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width < $300\mu s$, Duty Cycle < 2.0%

Typical Characteristics

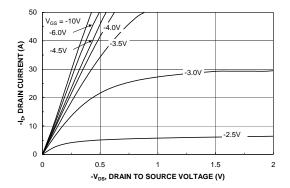


Figure 1. On-Region Characteristics.

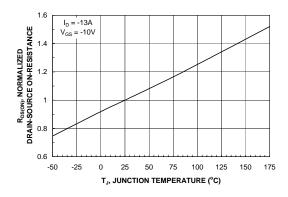


Figure 3. On-Resistance Variation with Temperature.

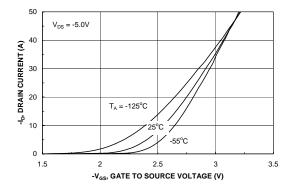


Figure 5. Transfer Characteristics.

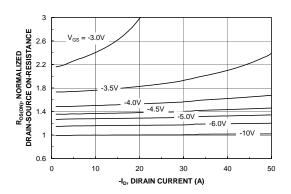


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

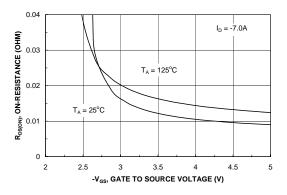


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

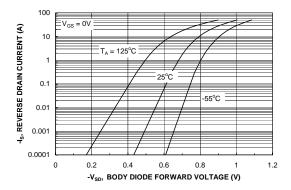
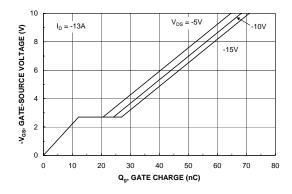


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



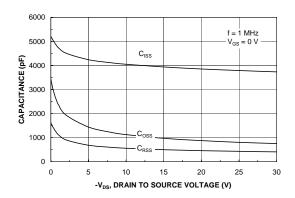
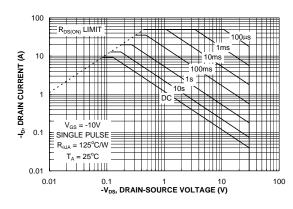


Figure 7. Gate Charge Characteristics.





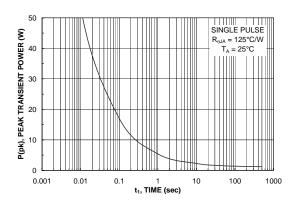


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

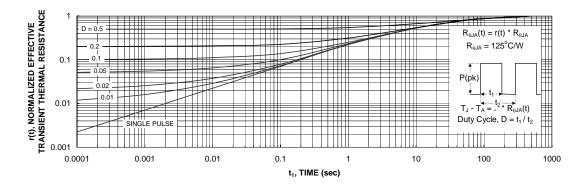


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

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